

DRICH PROTOTYPE





Two radiators with almost overlapping rings (to optimize the active area)

Configuration 1:

Aerogel ring

Configuration 2:

Gas (freon) ring

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Configuration 3:

Gas exchange / Vacuum

Cost estimates

Vacuum chamber (minimal elements, no mechanical processing):

- Mori meccanica: 4-5 kEUR
- Allectra: 5 kEUR (single chamber)
- VCS: 3.5 kEUR

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Mirrors: Edmund protected Aluminum

\bigcirc = 6'' (\sim 150 \text{ mm}) \text{ F}=1200 \text{ mm} 600 \text{ }

\bigcirc = 8'' (\sim 200 \text{ mm}) \text{ F}=1600 \text{ mm} 830 \text{ } (34 mm thickq8ness)

Support with micrometric screws: 1500- 2000 $
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GEMC simulations (docker) with geometry imported from CAD



H13700 READOUT (2018)

Derived from CLAS12 RICH readout:

- 1024 channels
- MAROC 64 channel parallel digitalization
- FPGA generated 1 ns timestamp
- DAQ protocol based on VME/VSX SSP





Custom adapter boards

- Compact distribution
- Use of existing MAROC boards
- Light and gas tightness



SIPM READOUT (2018)

SiPM might offer a cheaper and more efficient solution, expecially in a longer time perspective for other sectors

Robust device with low sensitivity to magnetic field Fast improvement in dark rate and cost but so far missing radiation hardness

Challenge: cooling integrated into the sensitive readout

Dedicated board for readout and cooling of a surface Mounting SiPM Matrix





PULSED LASER TEST BENCHES

Detailed characterization Sensors: gain, efficiency, cross-talk, radiation tolerance Electronics: gain, cross-talk, thresholds, time resolution

JLab

632 nm picosecond pulsed laser light Light diffuser to illuminate the whole MAPMT surface Standardized system with CLAS12 electronics H8500 6x6 mm² pixel sensor so far

INFN

632 nm and 407 nm picosecond pulsed laser light Light concentrator to scan the pensor surface Flexible layout supporting various sensors and Front-End electronics





SIPM RADIATION TOLERANCE

T. Tsang et al. JINST 11 (2016) P12002



I. Balossino et al. NIMA 876 (2017) 89

Single-photon capability after irradiation ?

S12572 standard technology S13360 trench technology



T= 0 C few 10⁹ n_{eq} cm²

Paolo Carniti @ RICH 2018



SiPM: Hamamatsu S13360-1350CS (50 µm cells)

Temperature: -30 °C

Bias: V_{BR} + 1.5 V

T= 84 K 10⁹ n_{eq} cm² Annealing at 250 °C